

PTO-1449		Application No.		Applicant(s): GORDON MA ET AL.			
Information Disclosure Citation in an Application		Docket Number		Group Art Unit		Filing Date	
		068736.0230				February 27, 2004	
U.S. PATENT DOCUMENTS							
		DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
<i>on</i>	1	4,811,075	03/07/89	Eklund	357	46	04/24/87
<i>on</i>	2	5,155,563	10/13/92	Davies et al.	357	23.4	03/18/91
<i>on</i>	3	5,252,848	10/12/93	Adler et al.	257	328	02/03/92
<i>on</i>	4	5,313,082	05/17/94	Eklund	257	262	02/16/93
<i>on</i>	5	6,168,983	01/02/01	Rumennik et al.	438	188	02/05/99
<i>on</i>	6	6,563,171	05/13/03	Disney	257	342	11/12/02
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
NON-PATENT DOCUMENTS							
		DOCUMENT (Including Author, Title, Source, and Pertinent Pages)					DATE
<i>on</i>	7	J.A. Appels and H.M.J. Vaes, "High voltage thin layer devices (RESURF devices)", IEDM technical digest, pp. 238-241					1979
<i>on</i>	8	H.M.J. Vaes and J.A. Appels, "High voltage high current lateral devices", IEDM technical digest, pp. 87-90					1980
<i>on</i>	9	T. Fujihira, "Theory of Semiconductor Superjunction Devices", Jpn. J. Appl. Phys., vol. 36, pp. 6254-6262					1997
<i>on</i>	10	G. Deboy, et al., "A new generation of high voltage MOSFETs breaks the limit line of silicon", IEDM technical digest, pp. 683-685					1998
<i>on</i>	11	A. Ludikhuizen, "A review of RESURF technology", Proc. of ISPSD, p. 11					2000
<i>on</i>	12	J. Cai, et al., "A novel high performance stacked LDD RF LDMOSFET, IEEE Electron Device Lett., vol. 22, no. 5, pp. 236-238					2001
<i>on</i>	13	J.G. Mena and C.A.T. Salama, "High voltage multiple-resistivity Drift-Region LDMOS", Solid State Electronics, Vol. 29, No. 6, pp. 647-656					1986
<i>on</i>	14	M.D. Pocha and R.W. Dutton, "A computer-aided design model for High-Voltage Double Diffused MOS (DMOS) Transistors", IEEE Journal of Solid-State Circuits, Vol. SC-11, No. 5					1976
<i>on</i>	15	I. Yoshia, et al., "Highly Efficient 1.5 GHz Si Power MOSFET for Digital Cellular Front End"; Proceedings of International Symposium on Power Semiconductor Devices & ICs; Tokyo, pp. 156-157					1992
<i>on</i>	16	Helmut Brech et al; "Record Efficiency and Gain at 2.1 GHz of High Power RF Transistors for Cellular and 3G Base Stations"; RF & DSP Infrastructure Division, Semiconductor Products Sector, Motorola, Tempe, Arizona					2003
EXAMINER					DATE CONSIDERED		
<i>Q96</i>					6-15-05		
EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.							